30. A semiconductor device according to claim 29, characterized in that said second substrate has the same thickness as said first substrate.

31. A semiconductor device according to claim 29 or 30, characterized in that said second substrate is made of the same material as said first substrate.

32. A semiconductor device according to claim 29, characterized in that the second substrate is one of a substrate having an insulating surface, an SOI substrate, and a silicon substrate.

33. A semiconductor device including at least a pixel portion, a data line side driver circuit, a scanning line side driver circuit, and a memory portion, characterized in that,

said pixel portion is formed on a first substrate,

said data line side driver circuit and said memory portion are formed on a second substrate,

said scanning line side driver circuit is integrally formed on a third substrate,

said second substrate and said third substrate are provided in a region except for said pixel portion on said first substrate and are connected with said pixel portion such that a signal from said data line side driver circuit and a signal from said scanning line side driver circuit are input to the pixel region, and

the semiconductor device has a function for displaying an image in accordance with image data stored in said memory portion.

34. A semiconductor device according to claim 33, characterized in that said second substrate and said third substrate have the same thickness as said first substrate.

35. A semiconductor device according to claim 33 or 34, characterized in that said second substrate and said third substrate are made of the same material as said first substrate.

36. A semiconductor device according to claim 33, characterized in that said second substrate and said third substrate are one of a substrate having an insulating surface, an SOI substrate, and a silicon substrate.

37. A semiconductor device according to any one of claims 28-30, 32-34, or 36, characterized in that said semiconductor device has a function of displaying a still image in accordance with the image data stored in said memory portion.

38. A semiconductor device according to any one of claims 28-30, 32-34, or 36, characterized in that said semiconductor device includes a memory control circuit, and

said memory control circuit and said memory portion are formed on the same substrate.

39. A semiconductor device according to any one of claims 28-30, 32-34, or 36, characterized in that said semiconductor device is composed of a first region having a function of displaying the image and a second region having a function of supplying the image data to said first region,

said first region includes the substrate on which the pixel portion is formed, and

the semiconductor device includes a first display method of displaying the image in accordance with the image data supplied from said second region and a second display method of displaying the image in accordance with the image data stored in the memory portion provided in said first region.

40. A semiconductor device of claim 39, characterized in that power consumed in said semiconductor device by said second display method is 70 % or lower of power consumed in said semiconductor device by said first display method.

41. A semiconductor device of claim 39, characterized in that when said second display method is performed, 50 % or higher of power consumed in said semiconductor device is consumed in said first region.

42. A semiconductor device of claim 39, characterized in that when said second display method is performed, 90 % or higher of power consumed in said semiconductor device is consumed in said first region.

43. A semiconductor device of claim 39, characterized in that said first display method is controlled by a CPU provided in said second region,

said second display method is controlled by a control circuit provided in said first region, and

said second display method can be performed with a state in which a power source of said CPU is turned off.

44. A semiconductor device group composed of a first semiconductor device having a function of displaying an image and a second semiconductor device having a function of supplying image data to said first semiconductor device,

said first semiconductor device is a semiconductor device according to any one of claims 28-30, 32-34, or 36, characterized in that,

said semiconductor device group includes a first display method of displaying the image data supplied from said second semiconductor device and a second display method of displaying the image in accordance with the image data stored in the memory portion included in said first semiconductor device.

45. A semiconductor device group of claim 44, characterized in that power consumed in the entire said semiconductor device group by said second display method is 70 % or lower of power consumed in said entire semiconductor device group by said first display method.

46. A semiconductor device group of claim 44, characterized in that when said second display method is performed, 50 % or higher of power consumed in said entire semiconductor device group is consumed in said first semiconductor device.

47. A semiconductor device group of claim 44, characterized in that when said second display method is performed, 90 % or higher of power consumed in said entire semiconductor device group is consumed in said first semiconductor device.

48. A semiconductor device group of claim 44, characterized in that said second display method can be performed by only said first semiconductor device.

49. A semiconductor device of any one of claims 28-30, 32-34, or 36, characterized in that said memory portion has a memory capacity of 100 kbit to 10 Gbit.

50. A semiconductor device according to any one of claims 28-30, 32-34, or 36, characterized in that said memory portion has a memory capacity of 1 Mbit to 128 Mbit.

51. A semiconductor device according to any one of claims 28-30, 32-34, or 36, characterized in that said memory portion is composed of one of an SRAM, a DRAM, and an EEPROM.

52. A semiconductor device according to any one of claims 28-30, 32-34, or 36, characterized in that said memory portion is composed of a combination of an SRAM, a DRAM, and an EEPROM.

53. A semiconductor device according to any one of claims 28-30, 32-34, or 36, characterized in that said semiconductor device is one of an active matrix liquid crystal display device, a passive matrix liquid crystal display device, an active matrix EL display device, and a passive matrix EL display device.

54. A semiconductor device according to any one of claims 28-30, 32-34, or 36, characterized in that said semiconductor device is one selected from a display, a video camera, a

head mounted display, a DVD player, a goggle type display, a personal computer, a cellular phone, and a car audio system. --